

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s):

Yi Ding

Assignee:

Mosel Vitelic, Inc.

Title:

Nonvolatile Memory Cell With Multiple Floating Gates Formed After

The Select Gate And Having Upward Protrusions

Application No.:

Filing Date:

July 30, 2003

Examiner:

Unassigned

10/632,186

Group Art Unit:

Unassigned

Docket No.:

M-15241 US

San Jose, California April 16, 2004

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR § 1.97(b)

Dear Sir:

Pursuant to 37 CFR § 1.56, § 1.97 and § 1.98, the documents listed on the accompanying form PTO-1449 are called to the attention of the Examiner for the above patent application. Copies of these documents are enclosed.

Citation of these documents shall not be construed as:

- 1. an admission that the documents are necessarily prior art with respect to the instant invention;
 - 2. a representation that a search has been made, other than as described above; or
- 3. an admission that the information cited herein is, or is considered to be material to patentability as defined in § 1.56(b).

No fee is believed to be required. If a fee is required for this Information Disclosure Statement, please charge the fee to Deposit Account No. 50-2257. This paper is being submitted in duplicate.

I hereby certify that this correspondence is being deposited with the United States Postal Service as First Class Mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on April 16, 2004.

Attorney for Applicant

Date of Signature

Respectfully submitted,

Michael Shenker

Attorney for Applicant(s)

Reg. No. 34,250

LAW OFFICES OF MacPherson, Kwok, Chen & Held LLP 1762 Technology Drive, Suite 226 San Jose, CA 95110 Telephone (408) 302-9520 Fax (408) 392-9262

U.S. Department of Commerce, Patent and Trademark Office					Atty Docket No. Serial No.					
The second of th								10/632,186		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT					Applicant					
						Yi Ding				
ADD 2.0.2007					Filing Date G			Group		
APR 2 0 2004					July 30, 2003		Unassigned			
*Examiner		Document	Dut	N	Class Subc		Filing Date lass If Appropriate			
Initial	AA	Number 6,420,231	Date 16 Jul. 2002	Name Harari et al.	Class Subc		ass II Appropriate			
	AB	2003/0218908 A1	27 Nov. 2003	Park et al.						
	AC	2004/0004863 A1	8 Jan. 2004	Wang				_		
	AD		0 0 0 0 0 0	,,,,,,			_,	_		
	AE					<u> </u>				
	AF									
	AG								-	
	AH		:	· · · · · · · · · · · · · · · · · · ·						
Foreign Patent Documents										
Translation										
	Document		Date	Country		Subclass		Yes	No	
	AI	EP 0 938 098 A2	25 Aug. 1999	Europe	Class					
	AJ									
	AK									
	AL									
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)										
AM United States Patent Application No. 10/798,475, entitled "Fabrication of Conductive Lines Interconnecting Conductive Gates in Nonvolatile Memories and Non-Volatile Memory Structures," Filed on March 10, 2004; Attorney Docket No. M-15296 US.										
	AN	AN United States Patent Application No. 10/797,972, entitled "Fabrication of Conductive Lines Interconnecting First Conductive Gates in Nonvolatile Memories Having Second Conductive Gates Provided By Conductive Gates Lines, Wherein The Adjacent Conductive Gate Lines For The Adjacent Columns Are Spaced From Each Other, And Non-Volatile Memory Structures," Filed on March 10, 2004; Attorney Docket No. M-15297 US.								
	AO				· · ·					
	AP		·	· · · · · ·						
F'			·	·					. "	
*EXAMINED: Initial if reference considers			Date Considered			DED (00 =				
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.										